





ZXMN3A01Z

#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT89 PACKAGE

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	<b>I<sub>D</sub> max</b> T <sub>A</sub> = 25°C (Note 5)	
30V	120mΩ @ V <sub>GS</sub> = 10V	3.3A	
	180mΩ @ $V_{GS} = 4.5V$	2.7A	

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- · Power Management functions
- Motor control

#### **Features and Benefits**

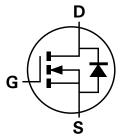
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

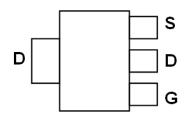
- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (approximate)







Device symbol



Pin-out Top

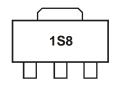
# **Ordering Information** (Note 3)

-					
	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXMN3A01ZTA	1S8	7	12	1,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**



1S8 = Product type Marking Code

ZXMN3A01Z

### Maximum Ratings @TA = 25°C unless otherwise specified

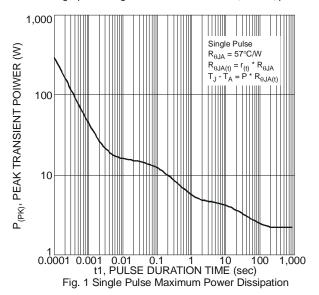
	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current	Steady State	@ V <sub>GS</sub> = 10V; T <sub>A</sub> = 25°C (Note 5) @ V <sub>GS</sub> = 10V; T <sub>A</sub> = 75°C (Note 5) @ V <sub>GS</sub> = 10V; T <sub>A</sub> = 75°C (Note 4)	I <sub>D</sub>	3.3 2.7 2.2	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	20	Α
Continuous Source Current (Body Diode) (Note 5)			I <sub>S</sub>	3.3	Α
Pulsed Source Current (Body Diode) (Note 6)			I <sub>SM</sub>	20	A

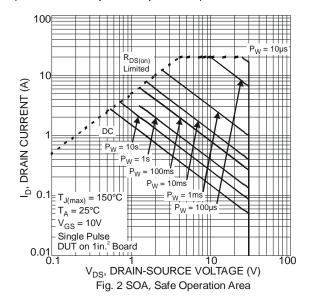
## Thermal Characteristics @TA = 25°C unless otherwise specified

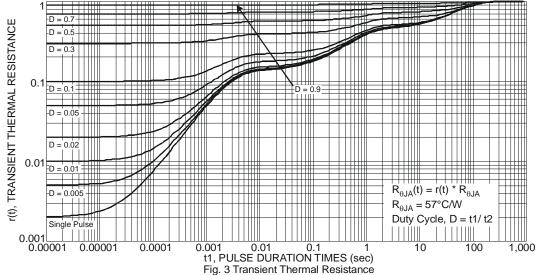
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	0	0.97	W
	(Note 5)	P <sub>D</sub>	2.12	W
Thermal Resistance, Junction to Ambient	(Note 4)	5	129	°C/W
	(Note 5)	$R_{\theta JA}$	59	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 4. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- 5. Device mounted on 25mm X 25mm FR-4 substrate PC board with 2oz copper
- 6. Single pulse rating 25mm x 25mm FR4 PCB, D=0.02, pulse width 300us pulse width limited by maximum junction temperature.







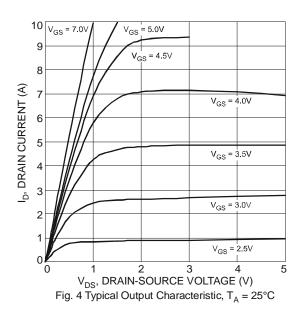


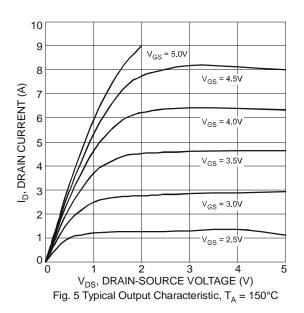
# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	0.5	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS					-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	-	-	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Ctatic Ducin Course On Desistence (Note 7)			0.106	120	mΩ	$V_{GS} = 10V, I_D = 2.5A$	
Static Drain-Source On-Resistance (Note 7)	R <sub>DS</sub> (ON)	-	-	180	11177	$V_{GS} = 4.5V, I_D = 2A$	
Forward Transconductance (Note 7 & 9)	g <sub>FS</sub>	-	3.5	-	S	$V_{DS} = 4.5V, I_{D} = 2.5A$	
Diodes Forward Voltage (Note 7)	V <sub>SD</sub>	-	0.85	0.95	V	$T_J = 25^{\circ}C$ , $I_S = 1.7A$ , $V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 8 & 9)	C <sub>iss</sub>	-	186	-	pF	), 05), ), 0),	
Output Capacitance (Note 8 & 9)	Coss	-	48	-	pF	$V_{DS} = 25V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance (Note 8 & 9)	C <sub>rss</sub>	-	29	-	pF	1 = 1.001112	
Gate Charge (Note 8 & 9)	Qg	-	2.6	-	nC	$V_{GS} = 4.5V$ , $V_{DS} = 15V$ , $I_D = 2.5A$	
Total Gate Charge (Note 8 & 9)	Qq	-	5.0	-	nC	101/11/	
Gate-Source Charge (Note 8 & 9)	Qgs	-	0.8	-	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Gate-Drain Charge (Note 8 & 9)	Q <sub>gd</sub>	-	1.2	-	nC	I <sub>D</sub> = 2.5A	
Reverse Recovery Time (Note 9)	t <sub>rr</sub>		17.7		ns	T <sub>J</sub> = 25°C, I <sub>S</sub> = 2.5A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 9)	Q <sub>rr</sub>		13.0		nC		
Turn-On Delay Time (Note 8 & 9)	t <sub>D(on)</sub>	-	2.6	-	ns		
Turn-On Rise Time (Note 8 & 9)	t <sub>r</sub>	-	4.1	-	ns	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 15V,	
Turn-Off Delay Time (Note 8 & 9)	t <sub>D(off)</sub>	-	13.5	-	ns		
Turn-Off Fall Time (Note 8 & 9)	t <sub>f</sub>	-	3.6	-	ns	<u> </u>	

Notes:

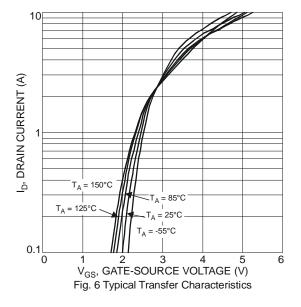
- 7. Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ . 8. Switching characteristics are independent of operating junction temperature. 9. For design aid only, not subject to production testing.

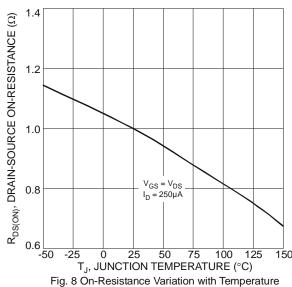


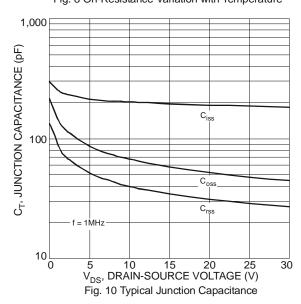


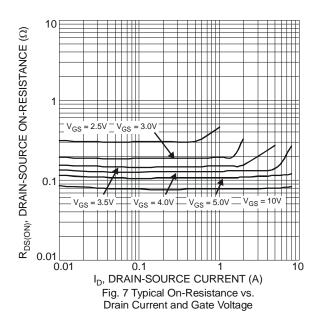


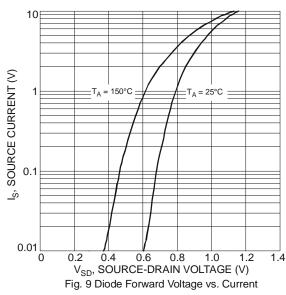
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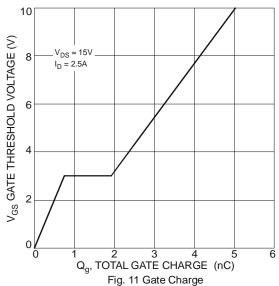






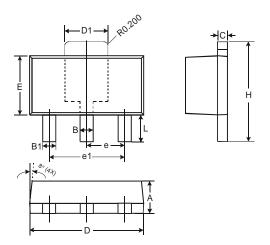






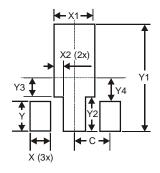


# **Package Outline Dimensions**



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.43		
D	4.40	4.60		
D1	1.52	1.83		
Е	2.29	2.60		
е	1.50 Typ			
e1	3.00 Typ			
Н	3.94	4.25		
L	0.89	1.20		
All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1 500





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